

## APPENDIX A

1. U.S. Patent Application 2002/0168820, Kozicki et al., published November 14, 2002, at Page 6 and Fig. 1, discloses a method of forming a microelectronic programmable device having an chalcogenide ion conductor formed between two electrodes. This application further discloses forming a chalcogenide ion conductor “using thermal and/or photo dissolution processing” (Page 5).

2. PCT Application WO 02/21542, Kozicki et al., published March 14, 2002, at Page 15 and Fig. 1, discloses a method of forming a microelectronic programmable device having an chalcogenide ion conductor formed between two electrodes. This application further discloses forming a chalcogenide ion conductor using “thermal and/or photo dissolution processing” (Page 11, lines 15-18).

3. PCT Application WO 00/48196, Kozicki et al., published August 17, 2000, at Page 8, lines 20-30 and Fig. 1, discloses a method of forming a microelectronic programmable device having an chalcogenide ion conductor formed between two electrodes. This application further discloses forming a chalcogenide ion conductor using “thermal and/or photo dissolution processing” (Page 7, lines 12-15).

4. U.S. Patent 6,418,049, Kozicki et al, filed Dec. 4, 1997, at Column 4, lines 28-67, discloses a “programmable sub-surface aggregating metallization structure” having a chalcogenide ion conductor and a plurality of electrodes. This patent further discloses forming a chalcogenide ion conductor using a photo dissolution process. (Column 4, lines 48-60).

5. U.S. Patent 5,761,115, Kozicki et al., filed May 30, 1996, at Columns 4-5, discloses a “programmable metallization cell” having a chalcogenide ion conductor and a plurality of electrodes. This patent further discloses forming a chalcogenide ion conductor using a photo dissolution process. (Column 5, lines 32-45).